

Sub
Cont

(d) generating a plasma of said etching gas at a second power level in said chamber and contacting said integrated circuit substrate with said second power level plasma for a second predetermined time, wherein said second power level plasma is a higher power plasma than said first power level plasma, and wherein said substrate has a CD loss decreased compared to the CD loss of a substrate formed by a method comprising said steps (a), (b) and (c) but not step (d).

B
End

Sub
B.

93. (New) The integrated circuit substrate of claim 92, wherein said CD loss is decreased by about 400 Angstroms.
